

CENTRAL INTELLIGENCE AGENCY

INFORMATION REPORT

This Document contains information affecting the National Defense of the United States, within the meaning of Title 18, Sections 793 and 794, of the U.S. Code, as amended. Its transmission or revelation of its contents to or receipt by an unauthorized person is prohibited by law. The reproduction of this form is prohibited.

SECRET

COUNTRY	East Germany	REPORT	<input type="text"/>	25X1
SUBJECT	Silicon Transistors to be Developed at VEB Werk fuer Fernmeldewesen and VEB Carl von Ossietzky	DATE DISTR.	23 April 1954	
DATE OF INFO.	<input type="text"/>	NO. OF PAGES	1	
PLACE ACQUIRED	<input type="text"/>	REQUIREMENT	<input type="text"/>	25X1
	<input type="text"/>	REFERENCES	<input type="text"/>	
	<input type="text"/>			25X1

This is UNEVALUATED Information

THE SOURCE EVALUATIONS IN THIS REPORT ARE DEFINITIVE.
THE APPRAISAL OF CONTENT IS TENTATIVE.
(FOR KEY SEE REVERSE)

25X1

1. After development of germanium transistors was removed from VEB Werk fuer Fernmeldewesen, Berlin Oberschoeneweide, at the order of the Russians, the enterprise received in early March 1954 a development order from the East German government for silicon transistors. The development is under the direction of Dr. Boehm (fnu).
2. VEB Carl von Ossietzky (Dralowid), which is engaged in development of germanium transistors, also started development of silicon transistors in mid-February 1954.

SECRET

STATE	x	ARMY	#x	NAVY	x	AIR	#x	FBI	AEC	ORR Ev	x	OSI Ev	x
-------	---	------	----	------	---	-----	----	-----	-----	--------	---	--------	---

(Note: Washington Distribution Indicated By "X"; Field Distribution By "#".)

25 YEAR RE-REVIEW

25X1